

BSK1040

Schottky Barrier Diode

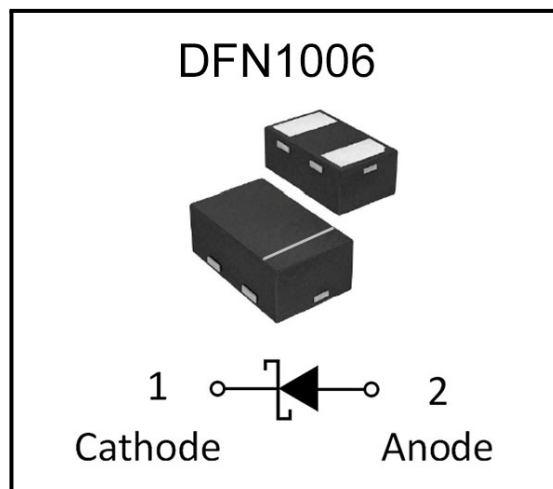
Features

- Low forward voltage drop
- High current capability
- High reliability
- High surge current capability
- Epitaxial construction

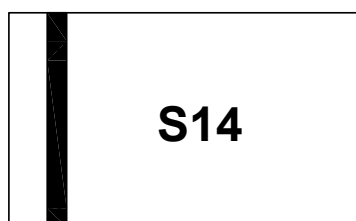
General Description

- Case: molded plastic
- Polarity: Color band denotes cathode
- Package: DFN1006 Plastic Package

Package



Marking



Ordering information

Order code	Package	Marking	Baseqty	Delivery mode
BSK1040	DFN1006	S14	10K	Tape and reel

Maximum Ratings@T_A=25°C unless otherwise noted

Symbol	Parameter	Limit	Unit
V _{RRM}	Maximum Recurrent Peak Reverse Voltage	40	V
V _{RMS}	Maximum RMS Voltage	28	V
V _{DC}	Maximum DC Blocking Voltage	40	V
I _{F(AV)}	Maximum average forward rectified current	1	A
I _{FSM}	Non-repetitive peak forward surge current 8.3ms singlehalf sine-wave	8	A
P _{tot}	Total Power Dissipation	150	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	400	°C/W
T _J	Operation Junction Temperature Range	-40 to +125	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C



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Electrical Characteristics@ $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V_F	Forward voltage	$I_F=0.2\text{A}$	—	—	0.4	V
		$I_F=1\text{A}$	—	—	0.6	V
I_R	Reverse voltage leakage Range	$V_R=10\text{V}$	—	—	40	μA
		$V_R=40\text{V}$	—	—	50	μA
C_J	Type junction capacitance	$V_R=4\text{V}, f=1\text{MHz}$	—	35	—	pF



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Typical Performance Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1: Forward Characteristics

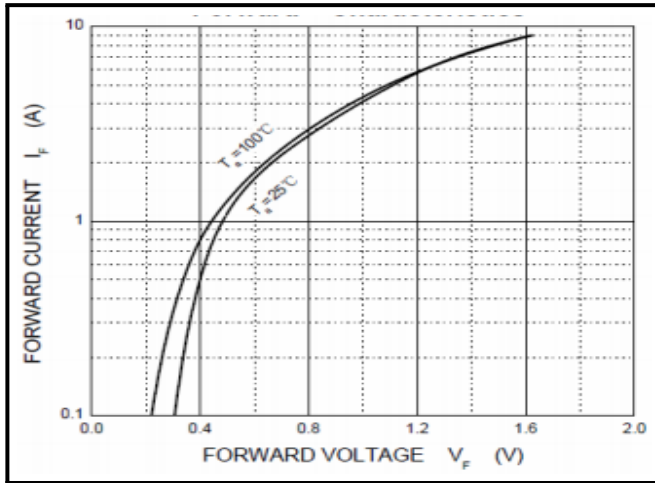


Figure 2: Reverse Characteristics

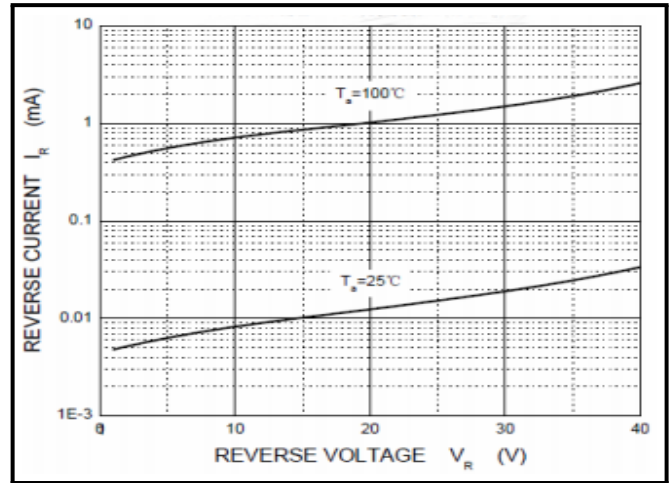
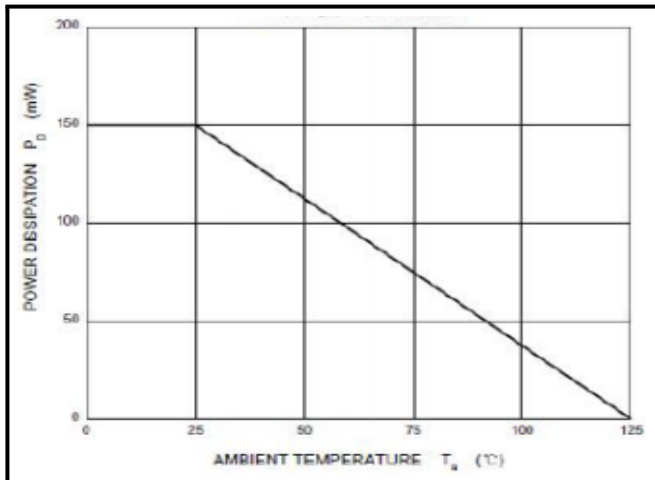


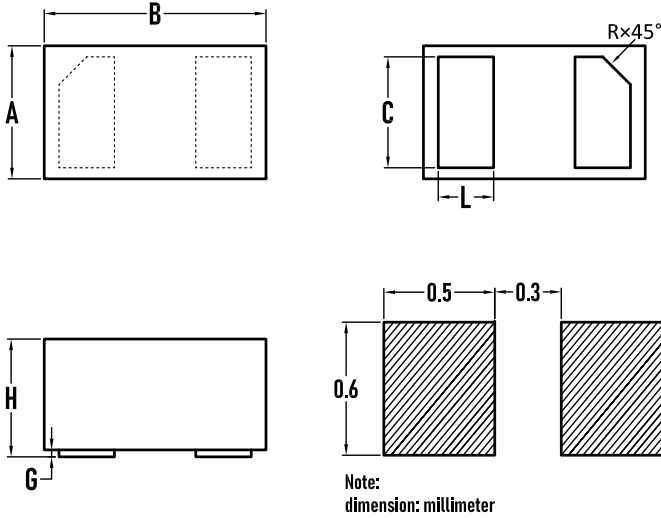
Figure 3: Power Derating Curve



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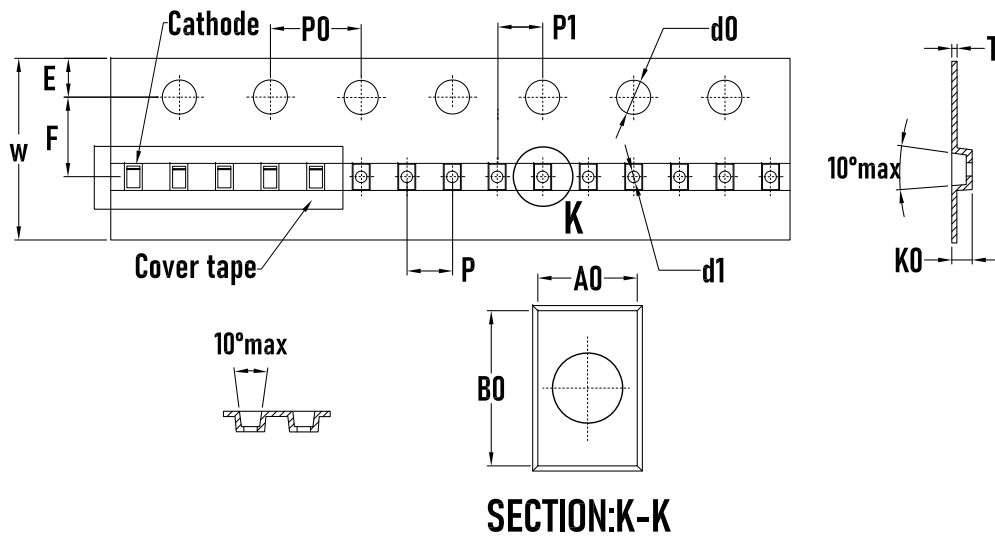
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Outline Drawing - DFN1006



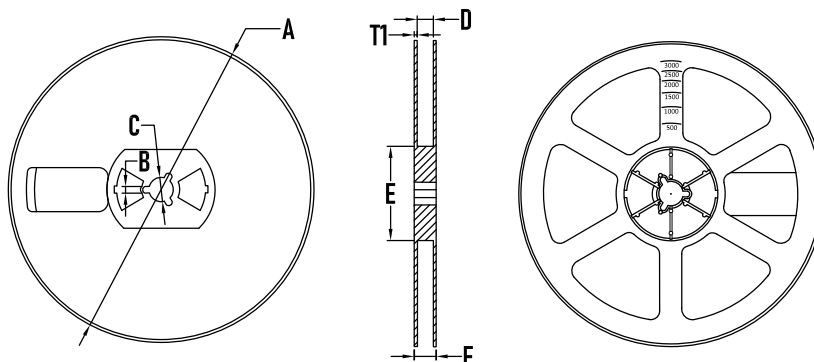
SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.55	0.60	0.65
B	0.95	1.00	1.05
C	0.45	0.50	0.55
L	0.20	0.25	0.30
F	0.05REF		
G	0.00	0.02	0.05
H	0.45	0.50	0.55
R	0.07	0.12	0.17

Packaging Tape - DFN1006



SYMBOL	MILLIMETER
A0	0.71±0.05
B0	1.11±0.05
d0	1.5 ^{+0.1} ₋₀
d1	0.50±0.05
E	1.75±0.10
F	3.50±0.05
K0	0.56±0.05
P	2.00±0.05
P0	4.00±0.10
P1	2.00±0.05
W	8.00 ^{+0.03} _{-0.01}
T	0.2±0.015

Packaging Reel



SYMBOL	MILLIMETER
A	178±1
B	3.5±0.2
C	14.3±0.2
D	9.8 ⁺² ₋₁
E	54.5±0.5
F	12.4±0.2
T1	1.0±0.2
Quantity	10000PCS

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

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